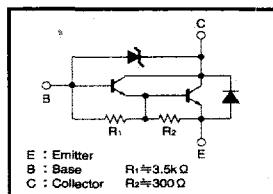


Medium Power Transistor (Motor relay or Solenoid drive)

2SD2212 / 2SD2143 / 2SD1866 / 2SD1764

●Features

- 1) Built-in zener diode between collector and base.
- 2) Strong protection against reverse surges due to low loads.
- 3) Built-in resistor between base and emitter.
- 4) Built-in damper diode.

●Circuit schematic**●Electrical characteristics ($T_a=25^\circ\text{C}$)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CEO}	50	—	70	V	$I_c = 50\mu\text{A}$
Collector-emitter breakdown voltage	BV_{CEO}	50	—	70	V	$I_c = 5\text{mA}$
Collector cutoff current	I_{CEO}	—	—	1.0	μA	$V_{\text{CE}} = 40\text{V}$
Emitter cutoff current	I_{EBO}	—	—	3	mA	$V_{\text{EB}} = 5\text{V}$
Collector-emitter saturation voltage	$\text{V}_{\text{CE(sat)}}$	—	—	1.5	V	$I_c/I_a = 1/\text{A}/1\text{mA}$
DC current transfer ratio	h_{FE}	1000	—	10000	—	$V_{\text{CE}} = 2\text{V}, I_C = 1\text{A}$
Output capacitance	C_{ob}	—	25	—	pF	$V_{\text{CE}} = 10\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$

* Measured using pulse current.

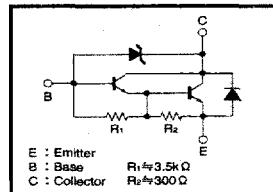
(96-762-D84)

Medium Power Transistor (Motor relay or Solenoid drive)

2SD1856

●Features

- 1) Built-in zener diode between collector and base.
- 2) Strong protection against reverse surges due to low loads.
- 3) Built-in resistor between base and emitter.
- 4) Built-in damper diode.

●Circuit schematic**●Electrical characteristics ($T_a=25^\circ\text{C}$)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CEO}	50	—	70	V	$I_c = 50\mu\text{A}$
Collector-emitter breakdown voltage	BV_{CEO}	50	—	70	V	$I_c = 5\text{mA}$
Collector cutoff current	I_{CEO}	—	—	10	μA	$V_{\text{CE}} = 40\text{V}$
Emitter cutoff current	I_{EBO}	—	—	3	mA	$V_{\text{EB}} = 5\text{V}$
Collector-emitter saturation voltage	$\text{V}_{\text{CE(sat)}}$	—	—	1.5	V	$I_c/I_a = 2\text{A}/2\text{mA}$
DC current transfer ratio	h_{FE}	2000	—	30000	—	$V_{\text{CE}}/I_c = 3\text{V}/2\text{A}$
Output capacitance	C_{ob}	—	75	—	pF	$V_{\text{CE}} = 10\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$

* Measured using pulse current.

●Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CEO}	60 ± 10	V
Collector-emitter voltage	V_{CEO}	60 ± 10	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_c	2	A (DC)
		3	A (Pulse) *1
Collector power dissipation	P_c	2	W *2
2SD2212		10	W ($T_c = 25^\circ\text{C}$)
2SD2143		1	W *3
2SD1866		20	W ($T_c = 25^\circ\text{C}$)
2SD1764		150	°C
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	$-55 \sim 150$	°C

*1 Single pulse $P_w = 10\text{ms}$ *2 On 40×40×0.7mm ceramic board.*3 Printed circuit board 1.7mm thick, collector plating 1cm² or larger.**●Packaging specifications and h_{FE}**

Type	2SD2212	2SD2143	2SD1866	2SD1764
Package	MPT3	CPT3	ATV	TO-220FP
h _{FE}	1k~10k	1k~10k	1k~10k	1k~10k
Code	T100	TL	TV2	—
Basic ordering unit (pieces)	1000	2500	2500	500

●Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CEO}	60 ± 10	V
Collector-emitter voltage	V_{CEO}	60 ± 10	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_c	5	A (DC)
		10	A (Pulse) *
Collector power dissipation	P_c	2	W
		25	W ($T_c = 25^\circ\text{C}$)
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	$-55 \sim 150$	°C

* Single pulse $P_w = 10\text{ms}$ **●Packaging specifications and h_{FE}**

Type	2SD1856
Package	TO-220FP
h _{FE}	2k~30k
Code	—
Basic ordering unit (pieces)	500

●Electrical characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CEO}	50	—	70	V	$I_c = 50\mu\text{A}$
Collector-emitter breakdown voltage	BV_{CEO}	50	—	70	V	$I_c = 5\text{mA}$
Collector cutoff current	I_{CEO}	—	—	10	μA	$V_{\text{CE}} = 40\text{V}$
Emitter cutoff current	I_{EBO}	—	—	3	mA	$V_{\text{EB}} = 5\text{V}$
Collector-emitter saturation voltage	$\text{V}_{\text{CE(sat)}}$	—	—	1.5	V	$I_c/I_a = 2\text{A}/2\text{mA}$
DC current transfer ratio	h_{FE}	2000	—	30000	—	$V_{\text{CE}}/I_c = 3\text{V}/2\text{A}$
Output capacitance	C_{ob}	—	75	—	pF	$V_{\text{CE}} = 10\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$

* Measured using pulse current.

(94L-885-D87)